Convenient real time monitor of the contamination of surface ion trap

Xinfang Zhang\textsuperscript{1,2}\textsuperscript{*}, Yizhu Hou\textsuperscript{1,2}, Ting Chen\textsuperscript{1,2}, Wei Wu\textsuperscript{1,2}\textsuperscript{†} and Pingxing Chen\textsuperscript{1,2}\textsuperscript{‡}

\textsuperscript{1}Department of Physics, College of Liberal Arts and Sciences, National University of Defense Technology, Changsha 410073, China
\textsuperscript{2}Interdisciplinary Center for Quantum Information, National University of Defense Technology, Changsha 410073, China

(Dated: November 14, 2019)

The anomalous heating of ions has been a major obstacle for quantum information processing (QIP) based on surface ion trap. Recent results indicated that the adatoms contamination on trap surface can generate contact potential, which gives rise to the fluctuating patch potential. By investigating the contamination from trap surface adatoms induced in loading process, we present the direct physical image of the contamination process and conclude the relationship between the capacitance change and contamination from surface adatoms through the theory and experiment. According to this relationship, the contamination from surface adatoms and the effect of in-situ treatment process can be monitored by the capacitance between electrodes in real time. This paper provides a research method of anomalous heating of ions, which has practical value to QIP based on surface ion trap.

I. INTRODUCTION

Anomalous heating has been widely observed experimentally in the surface ion traps\textsuperscript{[1,14]}, and as yet has not been explained clearly. Many studies have found that fluctuating patch potentials on the electrode is one of the major sources of the unexpectedly large heating rates\textsuperscript{[2,8,9,11,19]}. Patch potential can be mainly caused by two factors\textsuperscript{[2]}. light-induced charge on the substrate and surface adsorption on electrodes. In general, light-induced charge will discharge after a few days\textsuperscript{[5,7]}. In contrast, surface adsorption of atoms and molecules, especially atoms induced in loading process, will stay all the time\textsuperscript{[5,8,9]}.

Some previous experiments have shown that trap surface adatoms from exposure of the atomic beam generates the strong electric stray field\textsuperscript{[5,10]}, especially on the loading region of ions on surface ion trap\textsuperscript{[5]}. The change of the static electric fields will have the order of serval V/m\textsuperscript{[11]} in a few months, which also will introduce the high heating rate. Furthermore, the in-situ trap treatments to remove surface adsorption are shown in recent experiments\textsuperscript{[6,12]}. These treatments include ion milling to reduce heating rate up to 100 fold\textsuperscript{[13]}, pulsed-laser cleaning to reduce heating rate up roughly to 4 fold\textsuperscript{[2]}, and plasma treatment reduce heating rate up to approximately 3 fold\textsuperscript{[14]}. Although, the treatment processes are useful for surface ion traps, there are also inevitable limitations or damages\textsuperscript{[13]}. Ion milling would bring redeposition and engineering complexity to the experimental vacuum systems\textsuperscript{[5]}. Pulse-laser cleaning also could cause visible damages and light-induced charge on the substrate. Plasma cleaning would be mainly used to remove hydrocarbons from surface\textsuperscript{[14]}. In order to avoid damages of surface ion trap, the number of cleaning should be controlled appropriately. Thus, knowing when to clean trap surface and monitoring the cleaning effect are important to protect surface ion trap.

In this work, we investigate the contamination from surface adatoms induced in ion loading process. First, by test 10 trap samples, we find that the capacitance between electrodes, which can be directly and conveniently measured, can describe trap contamination from surface adatoms. Concretely speaking, with monolayer adatoms covering trap surface, the capacitance between electrodes increases approximately a few tenths of picofarad. The capacitance between electrodes, however, do not change before and after the deposition of monolayer atoms. Secondly, we give a description of the contamination process and explain the results above with the simulation and further experiment by atomic force microscope (AFM) and scanning electron microscope (SEM). Thus, we provide a simple method by measurement capacitance to estimate the contamination from surface adatoms.

II. EXPERIMENT AND SIMULATION OF TRAP SURFACE ADATOMS

Our ion loading scheme to load ions is shown as Fig.1(a), which is widely used in surface ion trap\textsuperscript{[4,15–18]}, in particular, the trap made of non-silicon substrate materials. Atoms leave from the atomic oven with a solid angle and form an atomic beam. The atomic beam sweeps across surface ion trap, and some atoms will be adsorbed on the surface then contaminate the trap. Many studies indicated that trapped ions suffer from the effect of surface adatoms\textsuperscript{[2,5,11,19]}, which will influence the trapping stability. Fig. 1(b) shows the circuit diagram of surface ion trap. In our study, the capacitance between two adjacent electrodes is monitored when atomic oven is turning on.
A. Experimental setup and results

Our surface ion trap is based on gold-on-silica fabrication technology, and the electrodes are 2.5μm thick gold, which have 10μm-wide gap between electrodes as shown in Fig.1(a). The experimental system contains the vacuum chamber, the calcium (Ca) oven and surface ion trap. Radio frequency (RF) electrode and ground electrode are connected to a two-pin electric feedthrough to monitor the capacitance variation by an LCR tester as shown Fig.1(b). The horizontal distance and vertical distance from calcium oven to trap centre are approximate 4cm and 1.5cm, respectively. The atomic beam generated by atomic oven sweeps across the trap surface. The calcium vapor pressure and the temperature of atomic oven can be adjusted. The surface adatoms will increase when the atomic oven turns on. The temperature of atomic oven is measured by a thermocouple, which is attached to the Ca atomic oven. The calcium vapor pressure at trap position is approximate $5 \times 10^{-4}$ Pa. Based on ten trap samples, We obtain the relationship between time of turning on atomic oven and capacitance between electrodes by repeating measurement process above. The initial capacitance between electrodes is about $2.5pF$. The values of the data points are taken from the average of ten trap samples’ capacitance at the same time of turning on atomic oven, as shown in Fig. 2, and the solid line is a guide to the eye. Each samples’ capacitance is about $2.5pF$ before turning on atomic oven. When turning on atomic oven for dozens of minutes, the capacitance between electrodes remain basically the same. Surprisingly, the capacitance sharply rises in the time of oven turned on for 70 mins, while it becomes stable after 90 mins. The maximin of capacitance difference is approximate 0.2pF, and the capacitance changes in a short time marked with the grey area in the Fig. 2. The measurement results reveal that the capacitance change between electrodes is closely related to the contamination from surface adatoms. Furthermore, we speculate that the mutation of capacitance change happens when the stage of monolayer film formation of adatoms.

B. Theoretical model and numerical simulation

In order to clearly understand the surface adatoms process, the theoretical model and numerical simulation was established. In the high vacuum, the properties of atomic gas can be described by the state equation of the ideal gas, which follows the Boltzmann distribution\textsuperscript{[20]}. In the pressure, P, we consider atoms of mass $m$ leave from the oven of temperature $T$ with a solid angle. Atoms leaving oven spread over the trap surface with distance $r$ at angle $\theta$ and normal angle $\beta$. The distribution of atoms on surface area $S$\textsuperscript{[21]} can be described as

- FIG. 1. (color online) (a) The picture shows a cut through the atomic beam with a solid angle sweeps across the surface ion trap. Atoms leave from the oven with an angle $\theta$ is spread over the trap surface with distance $r$ and normal angle $\beta$. (b) The circuit diagram of surface ion trap. The electrode gap is an equivalent capacitance, $C$, and the electrode is an equivalent resistance, $R$.

- FIG. 2. The variation of capacitance based on 10 identical trap samples are measured over time of turning on atomic oven, under the Ca vapor pressure $5 \times 10^{-4}$ Pa and the temperature 700K of atomic oven. The values of the data points are taken from the average of ten trap samples’ capacitance obtained by turning on oven for 5 mins and waiting for the vacuum to reach $10^{-7}$ Pa. The maximal capacitance difference is approximate 0.2pF.
Here, $\Phi$ is the leaving rate from oven per unit area and unit time, i.e. the outgoing flux, which can be described using the following expression:

$$D = \int_S \frac{\Phi \cos \theta \cos \beta}{\pi r^2} dS,$$

(1)

Where $\alpha$ is the evaporation coefficient, $N_A$ is the Avogadro’s number and $R$ is the universal gas constant.

The surface adatoms is simulated numerically by the finite element method (FEM) and is characterized by AFM and SEM. The thicker adatoms film will be observed clearly, which can also reduce the influence of surface roughness of the electrode or substrate, and can increase the accuracy of measuring film thickness. In order to verify the correctness of the theoretical model by characterizing adatoms thicker film, we adopt higher temperature, 900 K, to complete the adatoms experiment faster. and the corresponding Ca vapor pressure at trap position is approximate $3 \times 10^{-3} Pa$. These parameters are used in the simulation for different thickness of films on the surface. The simulation results in Fig. 3 show that the width of different thick films is always about 3.7um, and covering one side of the gap. There is no adatoms on another side of electrodes’ gap. The 3.7um-wide adatoms film will connect to the side of electrodes. Furthermore, the film thickness increases linearly with the exposure time of the atomic beam, as shown in the illustration.

According to the experiment, we perform the surface adatoms experiment for 13.5 h, whose parameters are consistent with the simulation’s. The obtained sample covering Ca film is tested by AFM, and the Ca film thickness is approximate 50 nm, as shown in Fig. 4. Due to the limited measurement range of AFM, we cannot scan the entire electrode gap. Fortunately, the SEM image of trap surface can show that the 10um-wide gap of electrodes is covered by 3.7um-wide Ca film, which is connecting to one side of the electrode, as shown in Fig. 5. These results are in agreement with the simulation, which also shows that our calculation is reliable. The change of capacitance between electrodes is also simulated by Comsol software for electromagnetic analysis. Based on the geometry of RF electrode and ground electrode on the silica substrate, the capacitance is simulated with RF electrode applied 1 V and ground electrode applied 0 V. The simulated capacitance difference with and without 3.7um-wide adatoms film is $0.2 pF$, which is consistent with experiment result.

According to the parameters of experiment, we simulated the surface adatoms with turning on atomic oven. The time forming Ca monolayer by simulation is about 65 min, which is close to the time when the capacitance starts to change. Because there is the temperature response process of atomic oven when we turn on and turn off oven in the experiment. Thus, the forming time of monolayer film by simulation is little shorter than that in experiment’s.

We can see that the capacitance starts to sharply increase after we turn on atomic oven for 70 mins, as shown in Fig. 2. The increase of capacitance indicates that the monolayer film is forming by surface adatoms on the surface ion trap. Therefore, the capacitance change is due to structural reorganization of trap electrode, which comes from the adsorbed film on electrode gap connecting to one side of electrode. In addition, the monolayer has been fully formed after turning on atomic oven for 90 min. Since there is only the variation of nanoscale thickness, which is negligible for electrode with several micrometers thick so that the capacitance between the electrodes doesn’t change anymore after turning on atomic oven more than 90 min.

In order to estimate the forming time of monolayer adatoms film for the ion-QIP experiment, we also simulate the surface adatoms induced in ion loading process under $10^{-5} Pa$ vacuum pressure and 500K temperature. We can get that the time of forming monolayer is approximate 3 months by continuously turning on atomic oven. If the atomic oven turn on for three hours each day in experiment, the surface ion trap can be used about two years before contamination from monolayer adatoms, which coincides with the time of unstably trapping ions in the Ref. [8].

The forming velocity of adatoms film depends on the temperature of atomic oven, which apply high, medium, and low temperature in our research. We adapt the high temperature, 900K, of atomic oven to rapidly form thick film which is used to compare simulations with experiments, and achieve a reliable theoretical model. At the medium temperature, 700K, the capacitance change trend can be quickly measured and clearly presented, which is also in agreement with corresponding simulated results based on theoretical model. During ion loading process, the Ca atomic oven usually apply low temperature, about 500 K, in the QIP experiment, and we give corresponding forming time of adatoms monolayer on surface ion trap.

### III. ANALYSIS AND DISCUSSION

The most direct physical image of the contamination process can be concluded from our study. In the ion loading process, the trap surface is expose to atomic beam. Atoms will be adsorbed and randomly distribute on surface. A monolayer film covering the electrode gap connect to one side of the electrode, which will result in the reconstructed electrode and the changed capacitance between electrodes. Though adatoms film will become more and more thicker during ion loading process, the electrode will be changed anymore. Though, the study of surface adatoms process is based on atomic oven, it is also suitable for laser ablation loading ions in surface ion
FIG. 3. (color online) The different adatoms thickness on the electrode gap is calculated in the Ca vapor pressure $3 \times 10^{-3} Pa$ and the temperature 900K of atomic oven. 10, 20, 30, 40, 50nm thick films are generated by turning on atomic oven for 2.7, 5.4, 8.1, 10.8, 13.5h, and the width of these adatoms films is always about 3.7um. The deferent thickness of adsorbent layer increases linearly with the exposure time to the atomic beam in the illustration.

FIG. 4. (color online) The 50nm thickness of the adsorbed atom film on the gap of electrodes tested by atomic force microscope, which comes from the atomic force microscope 3D image. There is the sharp increase precess at 2.7um position of scan range, which is the edge of adatoms film.

FIG. 5. (color online) Scanning electron microscope images of the surface ion trap with adsorbed atoms. The gap width of two electrodes is approximate 10um, which is covering a Ca atomic film with 3.7um width.

real-time, and is effective for simple structure of surface ion trap. Because the measurement of electric-field noise based on trapped ions is a numerous and complicated process of operation, and the surface adatoms is not the only reason for electric-field noise. Although, the electric-field noise can be measured by trapped ions to indirect describe the surface adatoms, it is unable to monitor in real-time and to reflect the adatoms film. In addition, our contamination measuring method for surface ion trap also can to be a new research means for anomalous heating of ions.

Because trapped ions suffer from high heating rate in surface ion trap, the trap surface should be cleaned by the treatments when the monolayer is formed, even though trap can still barely trap ions. In the process of in-situ treatments, the monitor of capacitance between electrodes can reflect the treatment effect and then can avoid the over cleaning which may damage surface ion trap and produce undesirable effects and ion-based QIP precisely.

IV. CONCLUSION

In the surface ion trap, we have obtained the relationship between the capacitance change and contamination from surface adatoms through the theory and experiment. Based on this relationship, we can measure the contamination from surface adatoms and the effect of the in-situ treatment process by monitoring the capacitance between electrodes in real time, which is valuable for trapping ion steadily.
ACKNOWLEDGMENTS

This work is supported by the National Basic Research Program of China under Grant No. 2016YFA0301903; the National Natural Science Foundation of China under Grant Nos. 11904402, 11874065, and 11574398, and the Research Plan Project of the National University of Defense Technology under Grant Nos. ZK18-01-01 and ZK18-03-04.

○ These authors contributed equally to this paper.

[28] D. Leibfried, R. Blatt, C. Monroe, and D. Wineland, Quantum dynamics of single trapped ions, Rev. Mod.